

2. (Amended) An electrode structure including a conductive film formed on an insulation film without penetrating the insulation film, the insulation film being formed on a base substrate, the insulation film comprising a first film of polyimide having a plurality of openings which reach the base substrate, a second film formed on inside walls of the openings and formed of an insulation material having a higher hardness than polyimide, and a plurality of poles of polyimide buried in the openings with the second film formed on the inside walls thereof.

3. (Amended) A semiconductor light-emitting device having an electrode structure including a conductive film formed on an insulation film without penetrating the insulation film, the insulation film being formed on a base substrate,

the insulation film comprising a plurality of poles of polyimide, a first film formed on side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on side surfaces thereof.

5. (Amended) A semiconductor light-emitting device having an electrode structure including a conductive film formed on an insulating film without penetrating the insulation film, the insulation film being formed on a base substrate,

the insulation film comprising a first film of polyimide having a plurality of openings which reach the base substrate, a second film formed on inside walls of the openings and formed of an insulation material having a higher hardness than polyimide, and a plurality of poles of polyimide buried in the openings with the second film formed on the inside walls thereof.

D3  
*Subj C*

7. (Twice Amended) A semiconductor light-emitting device according to claim 3, wherein the conductive film is formed on a third film of an insulation material without penetrating the third film, the third film is formed on the insulation film.

D4  
*Subj C*

8. (Twice Amended) A semiconductor light-emitting device according to claim 5, wherein the conductive film is formed on a third film of an insulation material without penetrating the third film, the third film is formed on the insulation film.

D5  
*Subj C*

13. (Twice Amended) A semiconductor light-emitting device including a waveguide, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide, the upper electrode having an electrode structure, the electrode structure including a conductive film formed on an insulation film without penetrating the insulation film, the insulation film being formed on a base substrate, the insulation film comprising a plurality of poles of polyimide, a first film formed on side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on the side surfaces thereof.

D6  
*Subj C*

14. (Twice Amended) A semiconductor light-emitting device including a waveguide, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide, the upper electrode having an electrode structure,

Amendment Accompanying RCE  
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the electrode structure including a conductive film formed on an insulation film without penetrating the insulation film, the insulation film being formed on a base substrate, the insulation film comprising a first film of polyimide having a plurality of openings a first film of polyimide having a plurality of openings which reach the base substrate, a second film formed on inside walls of the openings and formed of an insulation material having a higher hardness than polyimide, and a plurality of poles of polyimide buried in the openings with the second film formed on the inside walls thereof.